

General Description

The AAT8107 low threshold 20V, P-Channel MOS-FET is a member of AnalogicTech™'s TrenchDMOS™ product family. Using an ultra-high density proprietary TrenchDMOS technology the AAT8107 is designed for use as a load switch in battery powered applications and protection in battery packs.

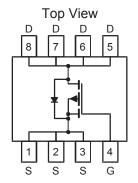
Features

- $V_{DS(MAX)} = -20V$ $I_{D(MAX)}^{1} = -6.5A @ 25^{\circ}C$
- Low $R_{DS(ON)}$:
 35 m Ω @ V_{GS} = -4.5V
 - 60 m Ω @ V_{GS} = -2.5V

SOP-8L Package

Applications Battery Packs

Battery-powered portable equipment



Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Symbol	Description		Value	Units	
V _{DS}	Drain-Source Voltage		-20	V	
V_{GS}	Gate-Source Voltage		±12		
I _D	Continuous Drain Current @ T _J =150°C ¹	$T_A = 25^{\circ}C$	±6.5		
		T _A = 70°C	±5.2	A	
I _{DM}	Pulsed Drain Current ²		±32	^	
I _S	Continuous Source Current (Source-Drain Diode) 1		-1.7		
P_{D}	Maximum Power Dissipation ¹	$T_A = 25^{\circ}C$	2.5	W	
		T _A = 70°C	1.6		
T _J , T _{STG}	Operating Junction and Storage Temperature Range		-55 to 150	°C	

Thermal Characteristics

Symbol	Description	Value	Units	
$R_{\theta JA}$	Typical Junction-to-Ambient steady state ¹	80		
$R_{\theta JA2}$	Maximum Junction-to-Ambient t<10 seconds ¹ 50 °C/W		°C/W	
$R_{\theta JF}$	Typical Junction-to-Foot ¹	27		

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Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Description	Conditions	Min	Тур	Max	Units
DC Charac	DC Characteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-20			V
R _{DS(ON)}	Drain-Source ON-Resistance ²	V _{GS} =-4.5V, I _D =-6.5A		27	35	mΩ
		V _{GS} =-2.5V, I _D =-5.0A		46	60	
I _{D(ON)}	On-State Drain Current ²	V _{GS} =-4.5V, V _{DS} =5V (Pulsed)	-32			Α
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_{D}=-250\mu A$	-0.6			V
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±12V, V _{DS} =0V			±100	nA
I _{DSS}	Drain Source Leakage Current	V_{GS} =0V, V_{DS} =-20V			-1	
		V _{GS} =0V, V _{DS} =-16V, T _J =70°C			-5	μA
g _{fs}	Forward Transconductance ²	V_{DS} =-5V, I_{D} =-6.5A		12		S
Dynamic C	haracteristics ³					•
Q_{G}	Total Gate Charge	V_{DS} =-15V, R_{D} =2.3 Ω , V_{GS} =-4.5V		13.6		
Q_{GS}	Gate-Source Charge	V_{DS} =-15V, R_{D} =2.3 Ω , V_{GS} =-4.5V		2.3		nC
Q_{GD}	Gate-Drain Charge	V_{DS} =-15V, R_{D} =2.3 Ω , V_{GS} =-4.5V		5.5		
t _{D(ON)}	Turn-ON Delay	V_{DS} =-15V, R_{D} =2.3 Ω , V_{GS} =-4.5V, R_{G} =6 Ω		10		
t _R	Turn-ON Rise Time	V_{DS} =-15V, R_{D} =2.3 Ω , V_{GS} =-4.5V, R_{G} =6 Ω		35		ns
t _{D(OFF)}	Turn-OFF Delay	V_{DS} =-15V, R_{D} =2.3 Ω , V_{GS} =-4.5V, R_{G} =6 Ω		38		115
t _F	Turn-OFF Fall Time	V_{DS} =-15V, R_{D} =2.3 Ω , V_{GS} =-4.5V, R_{G} =6 Ω		50		
Source-Drain Diode Characteristics						
V_{SD}	Source-Drain Forward Voltage ²	V _{GS} =0, I _S =-6.5A			-1.5	V
Is	Continuous Diode Current ¹				-1.7	Α

Note 1: Based on thermal dissipation from junction to ambient while mounted on a 1" x 1" PCB with optimized layout. A 10 second pulse on a 1" x 1" PCB approximates testing a device mounted on a large multi-layer PCB as in most applications. $R_{\theta JF} + R_{\theta FA} = R_{\theta JA}$ where the foot thermal reference is defined as the normal solder mounting surface of the device's leads. $R_{\theta JF}$ is guaranteed by design, however $R_{\theta CA}$ is determined by the PCB design. Actual maximum continuous current is limited by the application's design.

Note 2: Pulse test: Pulse Width = 300 μ s

Note 3: Guaranteed by design. Not subject to production testing.

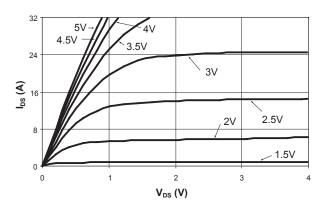
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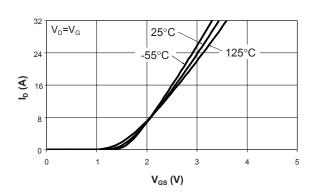
Typical Characteristics

(T_{.1} = 25°C unless otherwise noted)

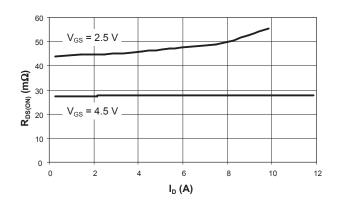
Output Characteristics



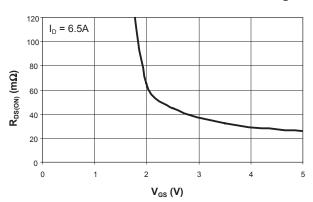
Transfer Characteristics



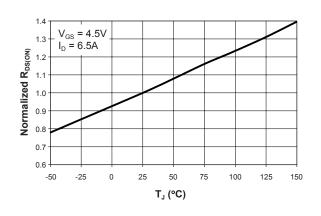
On-Resistance vs. Drain Current



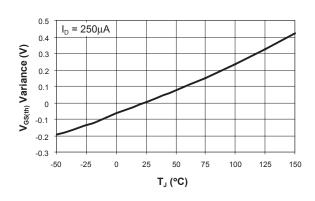
On-Resistance vs. Gate to Source Voltage



On-Resistance vs. Junction Temperature



Threshold Voltage



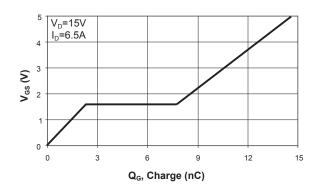
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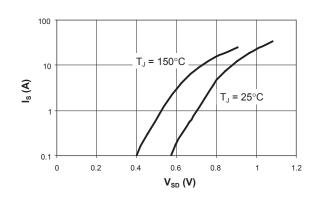
Typical Characteristics

(T_J = 25°C unless otherwise noted)

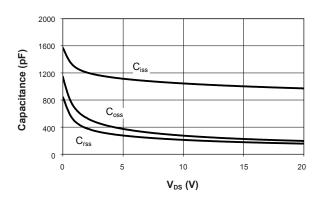
Gate Charge



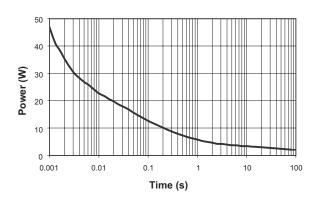
Source-Drain Diode Forward Voltage



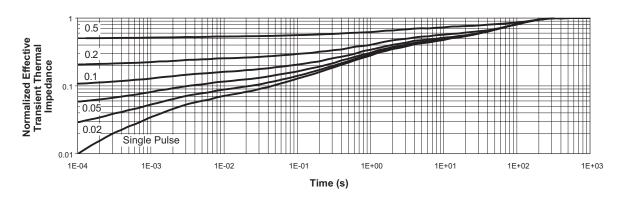
Capacitance



Single Pulse Power, Junction to Ambient



Transient Thermal Response, Junction to Ambient



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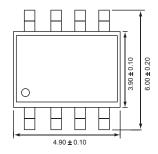
Ordering Information

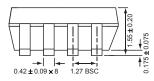
Package	Marking	Part Number (Tape and Reel)
SOP-8	8107	AAT8107IAS-T1

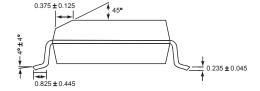
Note: Sample stock is generally held on all part numbers listed in BOLD.

Package Information

SOP-8







All dimensions in millimeters.

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